

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	210mΩ@10V	2A
	230mΩ@4.5V	

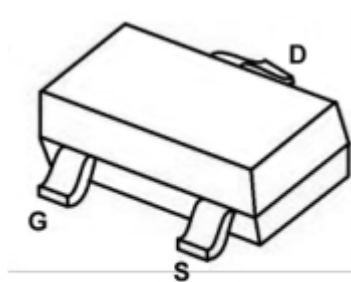
Feature

- Trench Technology
- Supper high density cell design
- Excellent ON resistance for higher DC current

Application

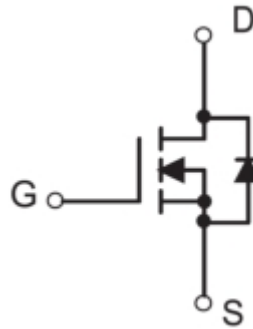
- Driver for Relay, Solenoid, Motor, LED etc.
- DC-DC converter circuit
- Power Switch
- Load Switch
- Charging

Package

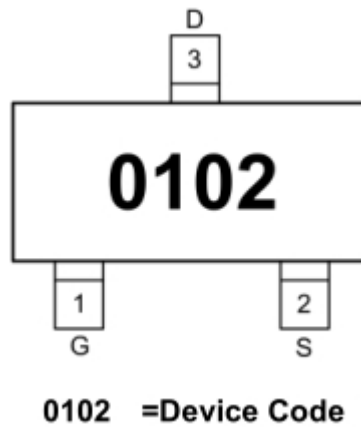


SOT-23

Circuit diagram



Marking



Absolute maximum ratings

($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	2	A
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}\text{C}$

Electrical characteristics

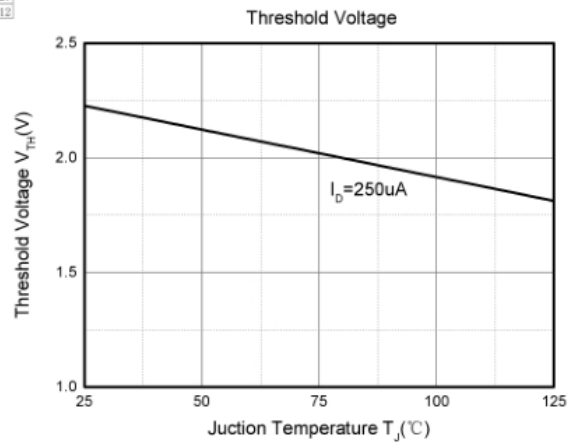
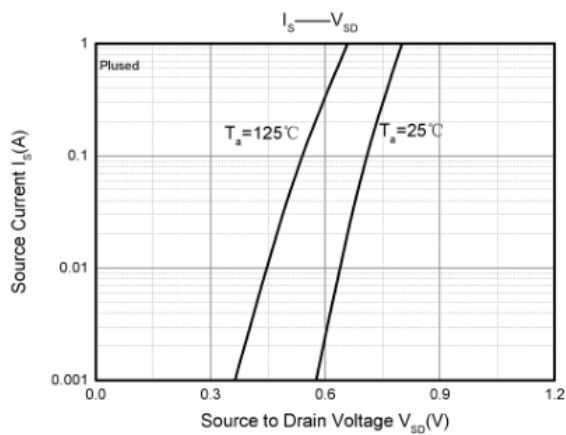
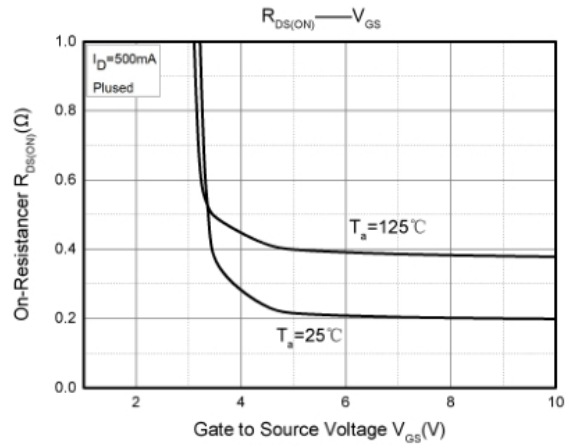
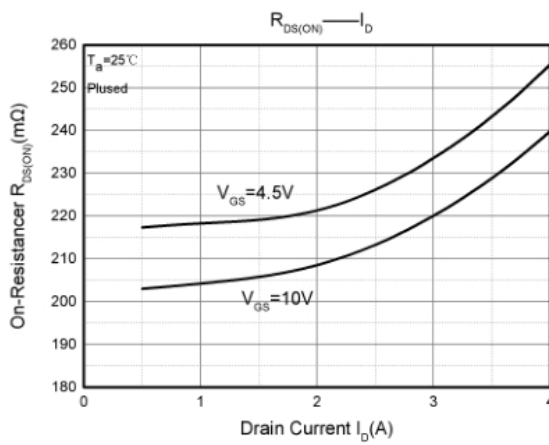
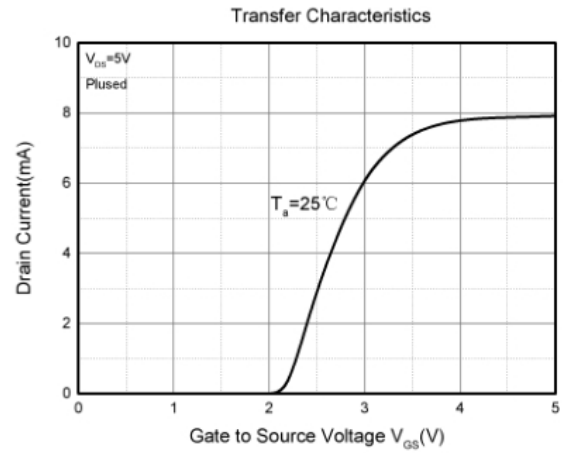
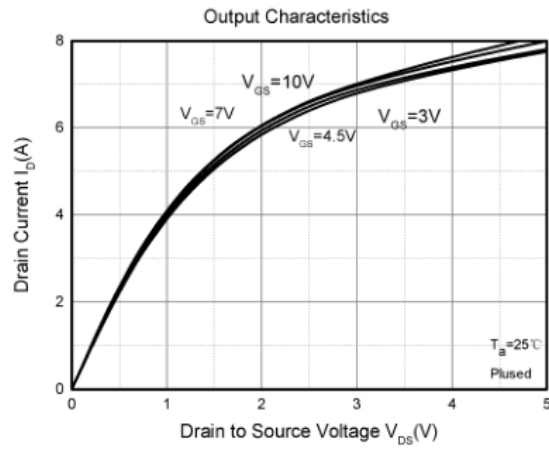
($T_A=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 100V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	μA
Gate threshold voltage ³	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	2.1	3	V
Drain-source on-resistance ³	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 1.4A$		210	240	m Ω
		$V_{GS} = 4.5V, I_D = 1.3A$		230	280	
Dynamic characteristics						
Input Capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V,$ $f=1MHz$		190		pF
Output Capacitance	C_{oss}			22		
Reverse Transfer Capacitance	C_{rss}			13		
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS}=50V, I_D=1.3A,$ $V_{GS}=10V$		5.2		nC
Gate-Source Charge	Q_{gS}			0.75		
Gate-Drain Charge	Q_{gd}			1.4		
Turn-On Delay Time	$T_{d(on)}$	$V_{DD}=50V, I_D=1.3A,$ $R_L=39\Omega, V_{GS}=10V,$ $R_G=1\Omega$		6		nS
Rise Time	T_r			10		
Turn-Off Delay Time	$T_{d(off)}$			10		
Fall Time	T_f			6		
Diode Characteristics						
Diode Forward Voltage ³	V_{SD}	$V_{GS} = 0V, I_s = 1A,$ $T_j = 25^{\circ}C$		0.8	1.2	V

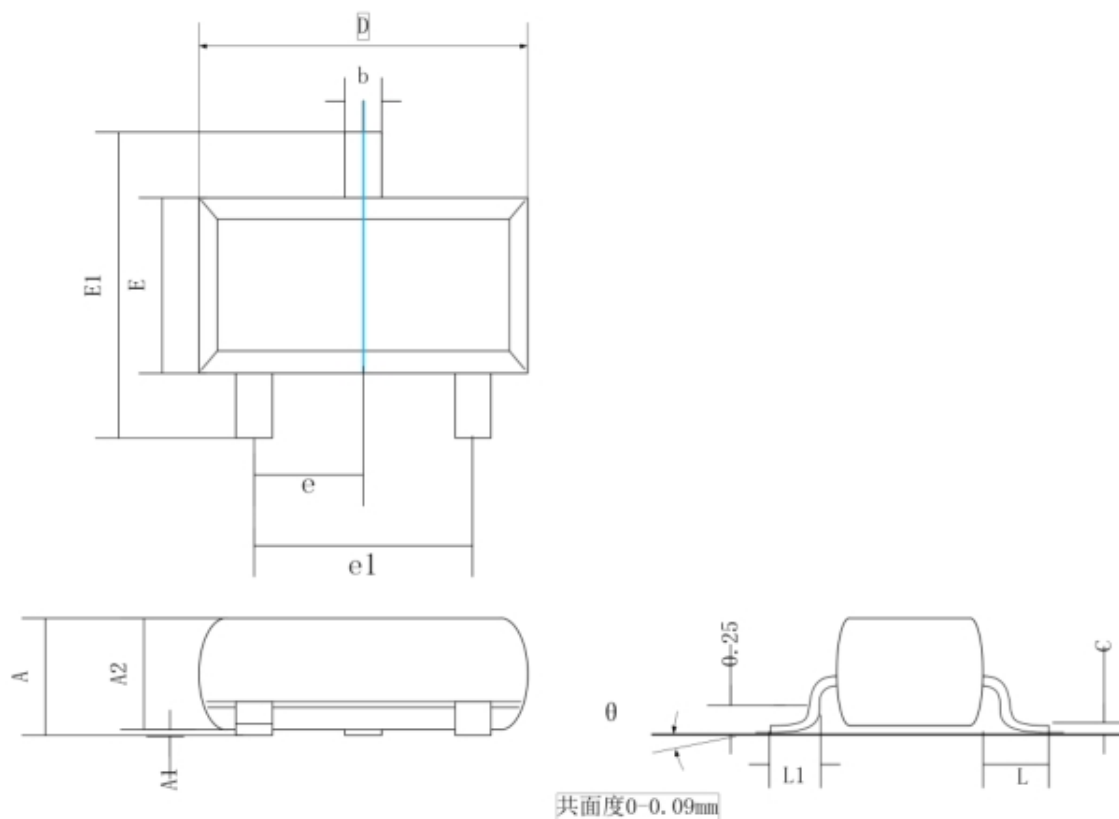
Notes:

- 1.Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2.Surface Mounted on FR4 Board, $t \leq 10$ sec.
- 3.Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
- 4.Guaranteed by design, not subject to production

Typical Characteristics



SOT-23 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50
θ	0°	8°